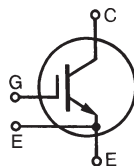


1200V XPT™ IGBT GenX3™

IXYN100N120C3

High-Speed IGBT
for 20-50 kHz Switching



$$V_{CES} = 1200V$$

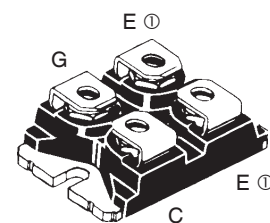
$$I_{C110} = 84A$$

$$V_{CE(sat)} \leq 3.50V$$

$$t_{fi(typ)} = 110ns$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	1200	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	160	A
I_{C110}	$T_C = 110^\circ C$	84	A
I_{CM}	$T_C = 25^\circ C$, 1ms	460	A
I_A	$T_C = 25^\circ C$	50	A
E_{AS}	$T_C = 25^\circ C$	1.2	J
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 200$ @ $V_{CE} \leq V_{CES}$	A
P_C	$T_C = 25^\circ C$	830	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
V_{ISOL}	50/60Hz	$t = 1min$	2500 V~
	$I_{ISOL} \leq 1mA$	$t = 1s$	3000 V~
M_d	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
Weight		30	g

SOT-227B, miniBLOC
E153432



G = Gate, C = Collector, E = Emitter
① either emitter terminal can be used as Main or Kelvin Emitter

Features

- Optimized for Low Switching Losses
- Square RBSOA
- Isolation Voltage 2500V~
- Positive Thermal Coefficient of $V_{ce(sat)}$
- Avalanche Rated
- High Current Handling Capability
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			10 μA
				1.25 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$	2.96		3.50 V
		3.78		V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	30	50	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		4950	pF
C_{oes}			356	pF
C_{res}			120	pF
$Q_{g(on)}$	$I_C = I_{C110}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		260	nC
Q_{ge}			47	nC
Q_{gc}			102	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C110}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$ Note 2		27	ns
t_{ri}			110	ns
E_{on}			12.00	mJ
$t_{d(off)}$			120	ns
t_{fi}			110	ns
E_{off}			4.90	mJ
$t_{d(on)}$		Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C110}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$ Note 2		27
t_{ri}			116	ns
E_{on}			15.00	mJ
$t_{d(off)}$			146	ns
t_{fi}			125	ns
E_{off}			6.15	mJ
R_{thJC}				0.18
R_{thCS}		0.05		$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
by one or more of the following U.S. patents:	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

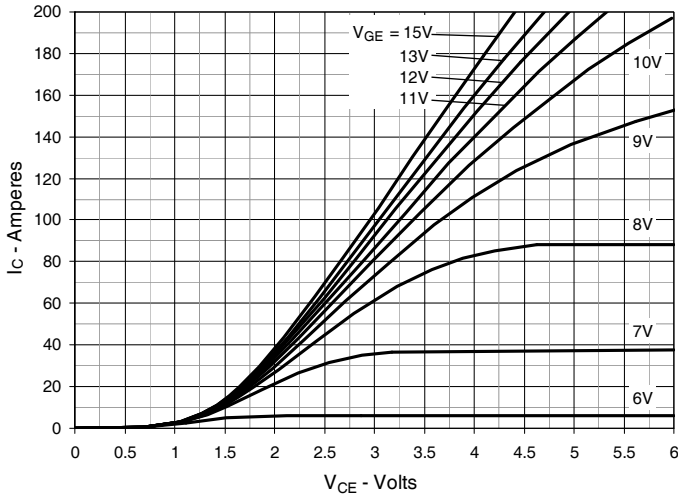
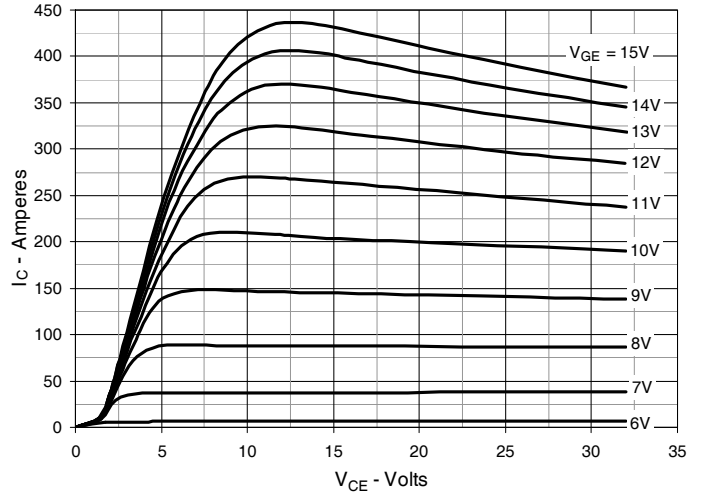
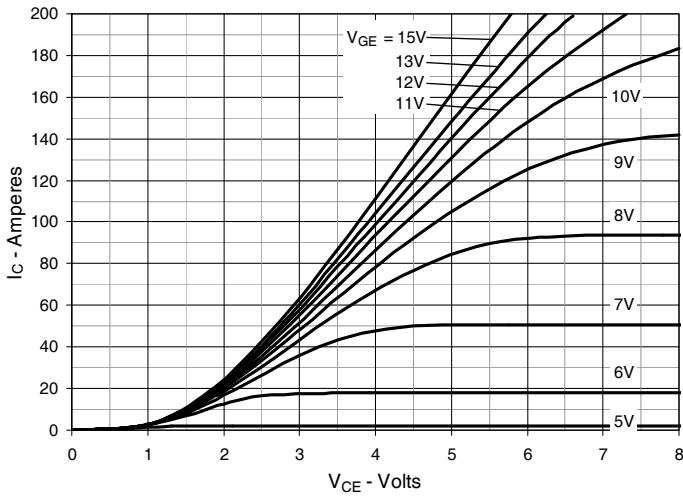
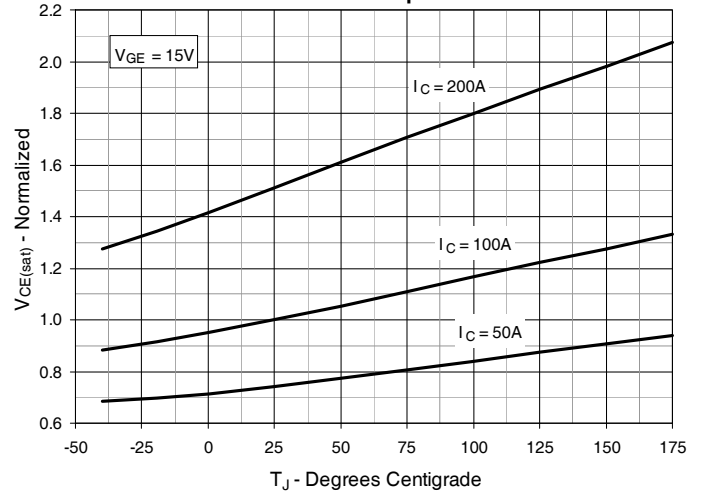
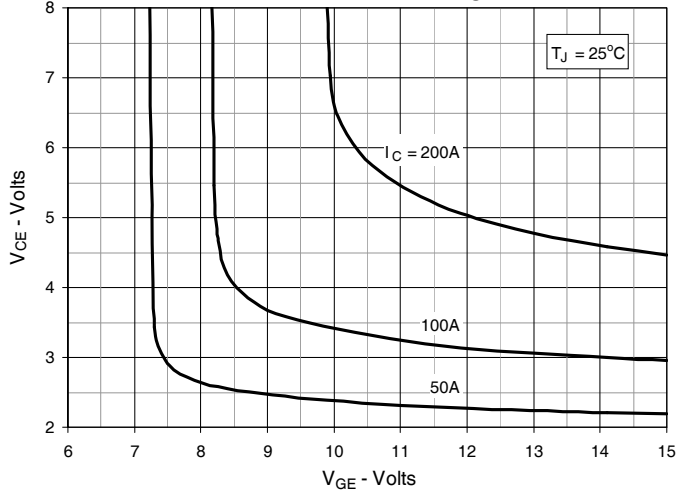
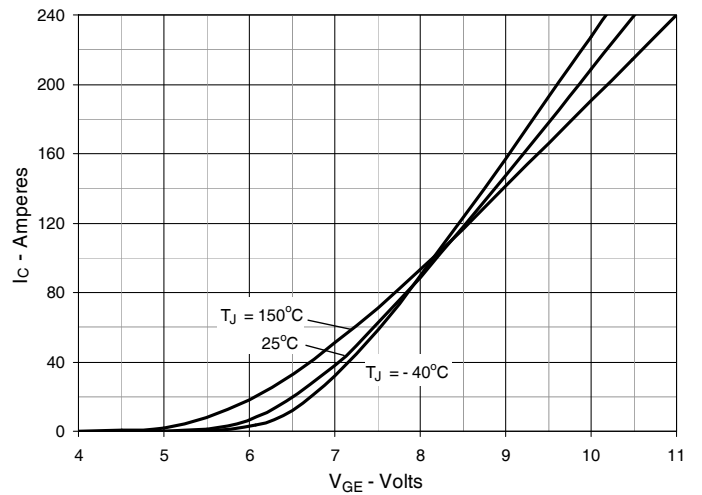
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


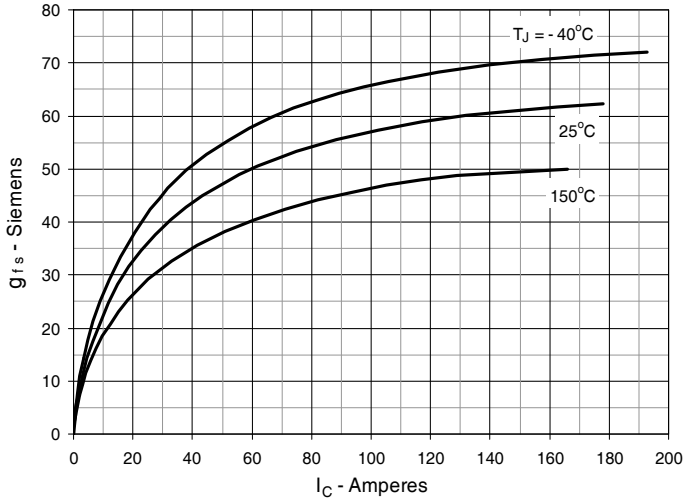
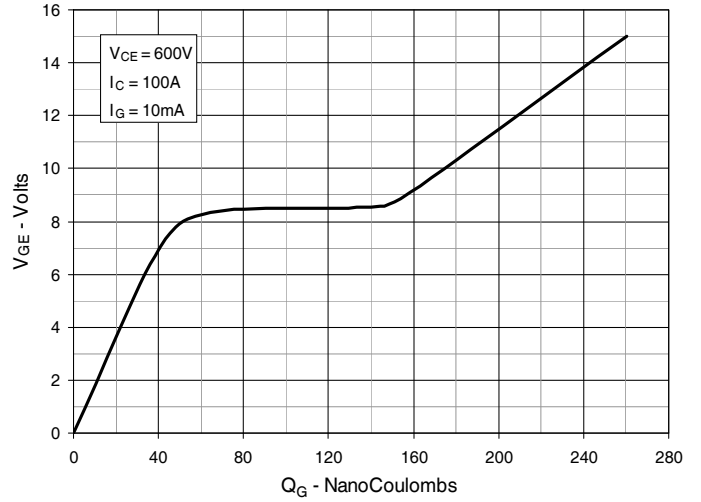
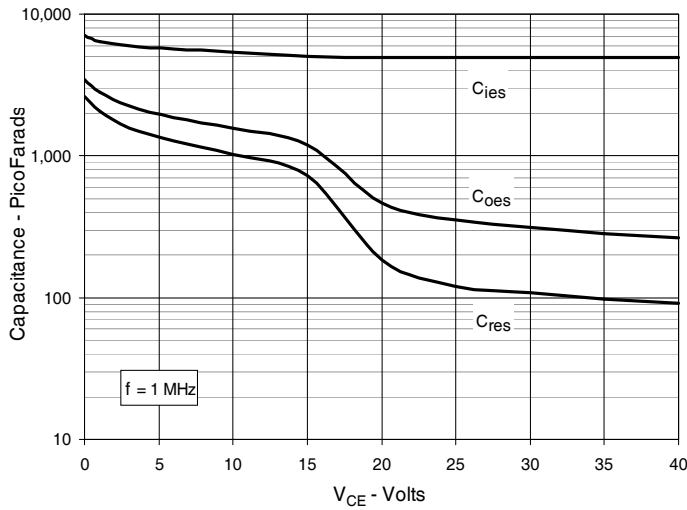
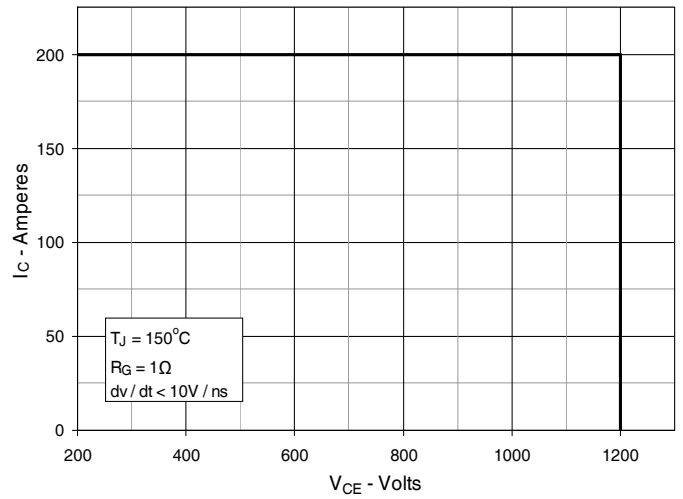
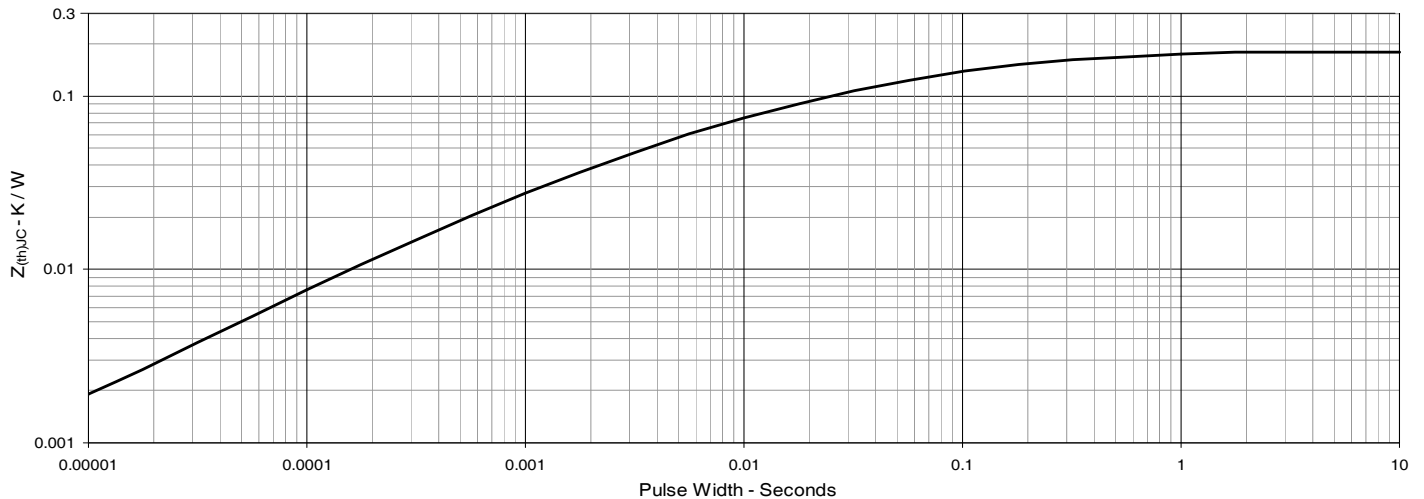
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance


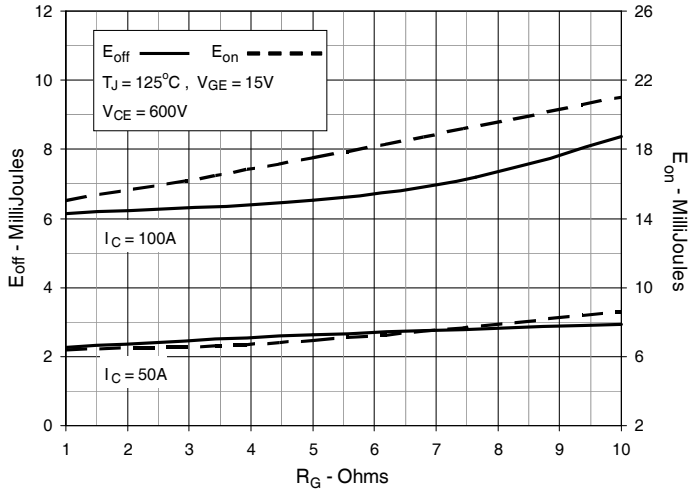
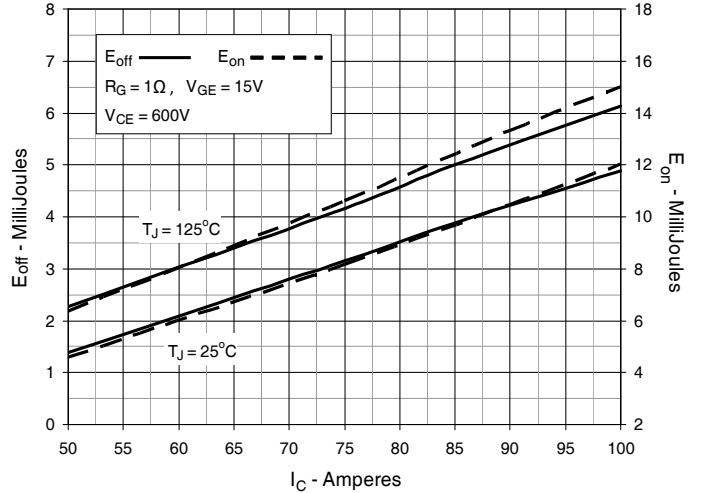
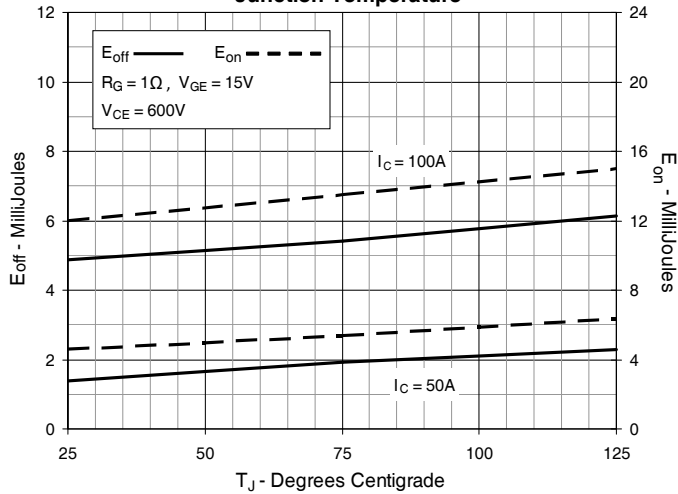
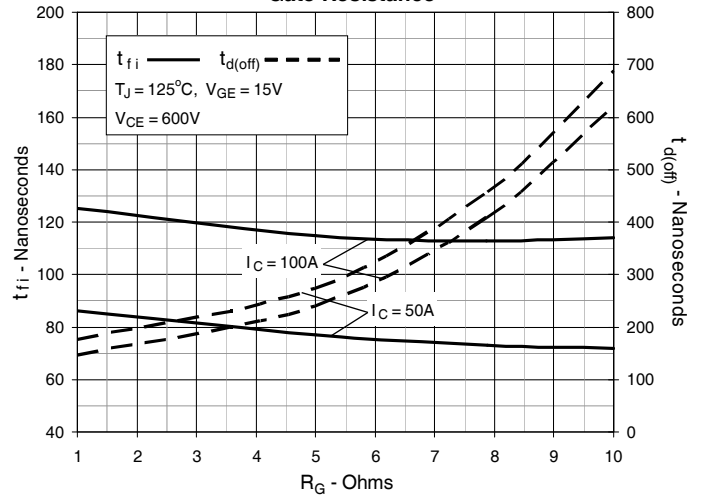
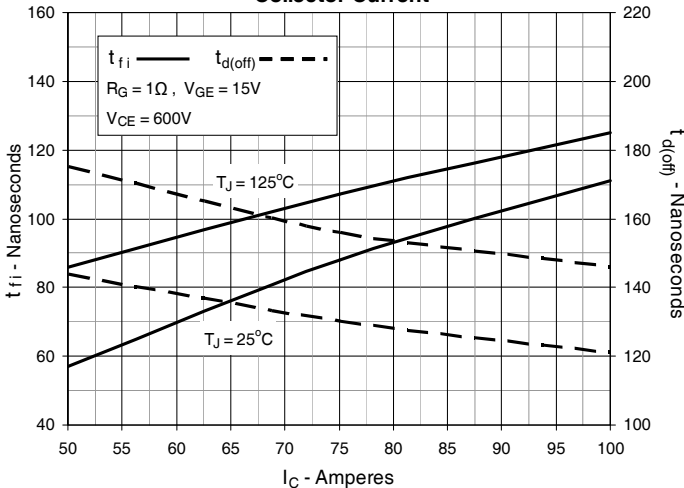
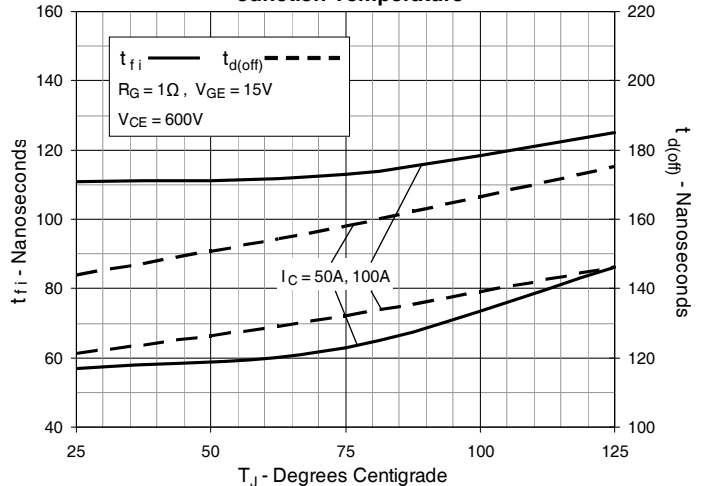
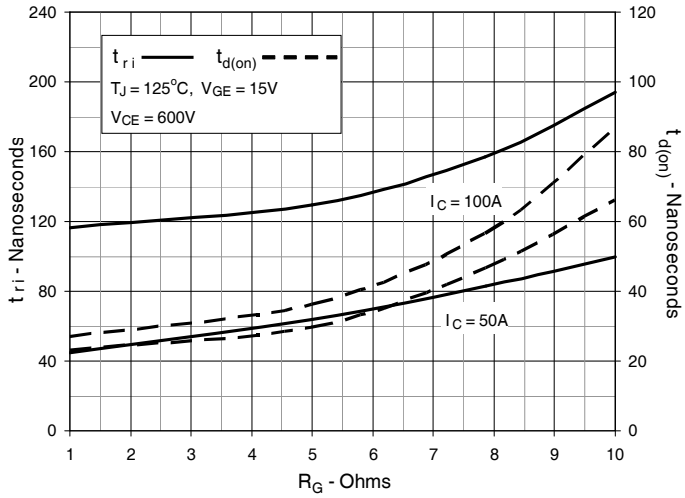
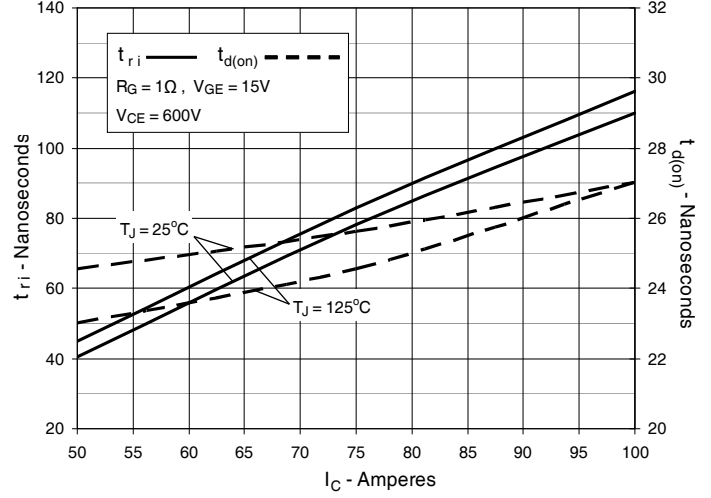
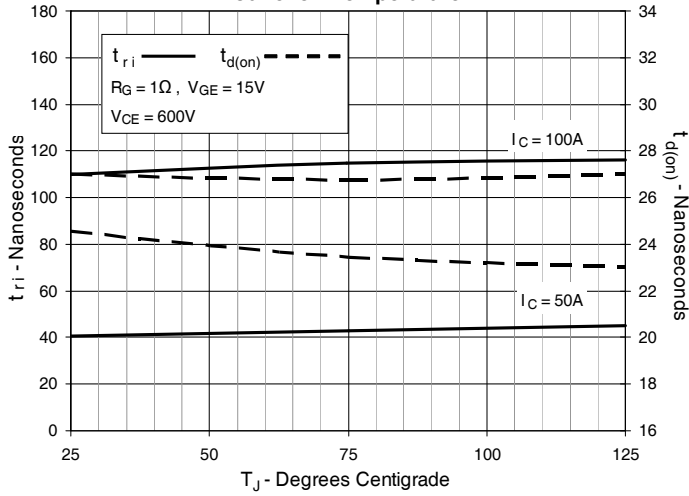
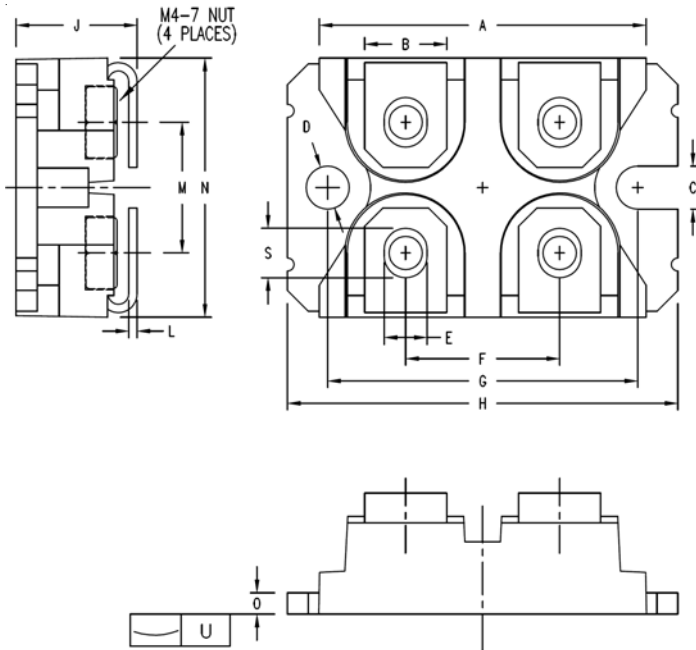
Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 13. Inductive Switching Energy Loss vs. Collector Current

Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature


SOT-227 miniBLOC (IXYN)


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.224	1.260	31.10	32.00
B	.303	.327	7.70	8.30
C	.161	.173	4.10	4.40
D	.161	.173	4.10	4.40
E	.161	.173	4.10	4.40
F	.587	.598	14.90	15.20
G	1.181	1.201	30.00	30.50
H	1.488	1.508	37.80	38.30
J	.461	.484	11.70	12.30
L	.030	.033	0.75	0.85
M	.492	.512	12.50	13.00
N	.984	1.004	25.00	25.50
O	.075	.087	1.90	2.20
S	.181	.193	4.60	4.90
U	.000	.005	0.00	0.13

- NUT MATERIAL:**
 STANDARD - Low carbon steel with Ni plating.
 OPTIONAL: - Brass Nut is available.
 PART NUMBER-BN
- ALL METAL SURFACE ARE PRE NI PLATED EXCEPT TRIM AREA.**